

# Total Ionizing Dose Report

### Apogee AP54RHC Product Family

30 krad (Si)

This report covers the radiation characterization results for the devices in the AP54RHC product family. The report specifies the measured performance impact of TID (Total Ionizing Dosage) up to 30krad(Si). The results show that the devices passed all parametric measurements within the specified limits.

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## 1 Scope

The report covers the AP54RHC family, and it details the test procedures, the measurement and irradiation test setups, and the measured characteristics of the devices before and after being irradiated. The reported measurement results show that the devices have excellent performance for low-earth-orbiting (LEO) and other applications up to 30krad (Si).

# 2 Tested Devices

AP54RHC11 (Triple 3-input AND) and AP54RHC27 (Triple 3-input NOR) were tested. These parts were burned-in for 240 hours at 125°C in accordance with MIL-STD-883J, Test Method 1015.10 prior to TID exposure. The burn-in oven, located at Apogee's Plano based electronics lab is shown in Figure 1 and Figure 2.



Figure 1: Burn-in apparatus



Figure 2: Burn-in Oven Internal

Although the AP54RHC11 and AP54RHC27 were the only parts tested in the AP54RHC family, the remaining parts of the family are Qualified By Similarity given that all parts in the family use the same base silicon layers. A single top level metal layer is used to set the boolean functionality and is the only difference between die in the members family, as shown in Figure 6.

# 3 Irradiation and Testing Setups and Procedure

#### 3.1 Irradiation Facility and Equipment

VPTrad, based in Chelmsford, Massachusetts, served as the irradiation facility and provided an exposure report dated August 20th, 2020 [2]. As specified there, the dosimetry equipment was based on the BioSpin e-scan from Bruker [3], and the source was a Gammacell GC220 Cobalt 60 irradiation unit [4], shown in Figure 3 below. The irradiation rate was 126 rad(Si)/s and the rate at calibration was 136 rad(Si)/s  $\pm 6\%$ , as per a calibration performed on January 3rd, 2020. Figure 4 shows one of the biasing boards that was used to bias the devices during the irradiation. The jumpers shown in the photo were used to create the desired biasing conditions for each of the 2 different boards. The boards, referred to as "Board #2 and Board #3" in the VPTrad report, were irradiated at incremental TID levels, and the devices were removed at specific dosage levels as detailed in Table 1.The devices remained in these boards while being shipped to the testing



facility, such that the identity of the tested devices and the TID levels they were exposed to could be easily confirmed.



Figure 3: Cobalt 60 irradiation unit



Figure 4: Biasing board used in irradiation

#### 3.2 Measurement Setup

The devices went through pre-radiation and post-radiation DC parametric and functional testing at the facility of Apogee Semiconductor in Texas. The devices were tested in a semi-automatic benchtop screening board interfacing with Keithley 2400 SMUs (Source Measurement Unit) as shown in figure 5. The calibration certificates of all instruments used can be found in appendix A.

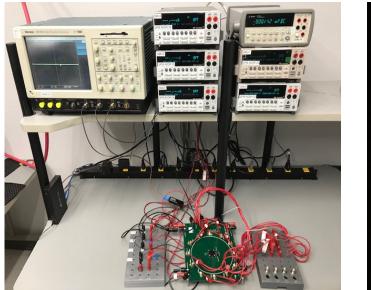


Figure 5: Apogee benchtop screening board

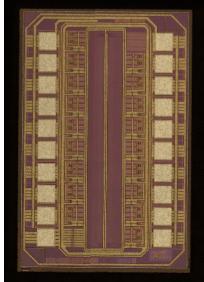


Figure 6: Apogee AP54RHC Family Die



#### 3.3 Test Procedure

The TID irradiation test was done in accordance with the procedures outlined in MIL-STD-883-1 (Testing Method 1019.9) [5]. During the irradiation at the VPTrad facility, the tested devices were all biased such that their inputs were tied to either GND or to VDD (3.3V or 5V), to validate all possible bias conditions during the exposure for common VDD expected in most applications. The boards were exposed to increasing TID levels at VPTrad, Chelmsford, Massachusetts and the devices were then removed from the biasing boards at corresponding dosage levels, as specified in Table 1. They were then packed in a pillowstat box and shipped overnight in dry ice to the testing facility, Apogee Semiconductor's lab in Texas. Upon arrival, the devices were unpacked from the dry ice and allowed to warm to ambient/room temperature. These parts were then tested using the measurement setup described above. The characteristics recorded for each tested device were compared against what was recorded for it at the same setup prior to its irradiation, as shown in Figure 7 and Figure 8.

VDD (V)	Device Type	Device Serial Number	DUT #	Dosage (krad (Si))
	AP54RHC11	819	1	10
	AP54RHC11	498	2	10
	AP54RHC11	839	3	20
	AP54RHC11	813	4	20
5	AP54RHC11	808	5	30
0	AP54RHC11	844	6	30
	AP54RHC11	810	7	35
	AP54RHC11	822	8	35
	AP54RHC11	824	9	45
	AP54RHC11	801	10	45
	AP54RHC27	740	11	20
	AP54RHC27	717	12	20
3.3	AP54RHC27	739	13	35
0.0	AP54RHC27	712	14	35
	AP54RHC11	831	15	45
	AP54RHC11	807	16	45

Table 1: List of tested devices and corresponding dosage levels

### 4 Test Results

The parametric and functional results of both the AP54RHC11 and the AP54RHC27 devices pass for all biasing conditions and across all dosage levels. At TID levels below the specified 30krad(Si) rating for the AP54RHC Family, the maximum shift in  $I_{DD}$  (quiescent power supply current) observed was below 1%. At TID levels greater than the specified 30krad(Si) limit, the  $I_{DD}$  current was observed to exhibit a small increase in current, but still well within the product datasheet limits. These results are visualized in Figure 7 and Figure 8. There was no significant shift (<1%) observed in the other measured parameters accross all the radiation levels and biasing conditions. It was noted that DUT 8 and DUT 15 had input pins that were pulling excessive amount of current, which is indicative of electrical overstress on the gate oxides. Therefore, their results have been omitted from this report. At the time of publication of this report, the 2 units exhibiting electrical overstress had been submitted to the failure analysis lab. The results of this will be published in a separate report.



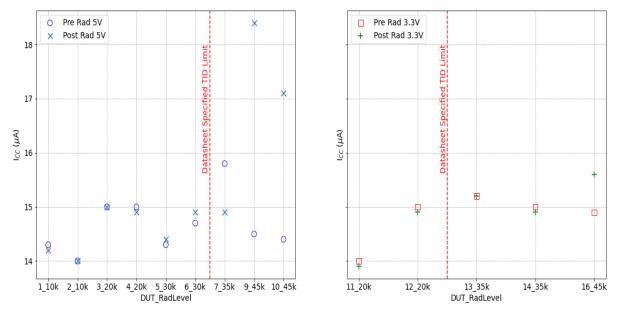


Figure 7: Pre radiation and post radiation power supply current all outputs HIGH

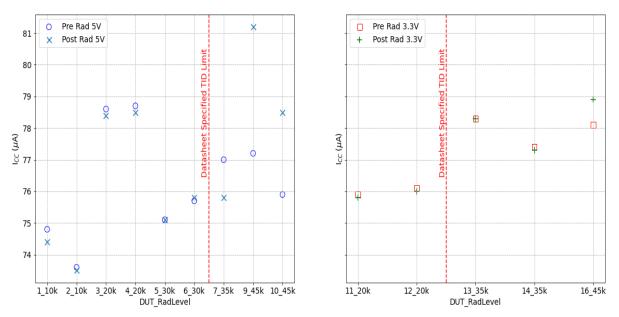


Figure 8: Pre radiation and post radiation power supply current all outputs LOW



# 5 Exposure Report from VPTrad

	Radiatio									
S	Apogee Sen 538 Haggaro Suite 406 Plano, TX 7	d Str	reet					August 20, 20	20	
S	Subject:			Exp	posure <u>Re</u>	port				
L	ob#:			2018	25					
	Product:				OUT Boards					
1975	rradiation I	Date		2000000000	0/2020					
1000	Source Num				20 #136R					
						scan # SC0424				
J.					ıker Biospin escan # SC0424 IST) 06/21 (Batch # T030901)					
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### 6 Revision History

REVISION	DESCRIPTION	DATE
A00	Initial internal release.	September 5, 2020

For the latest version of this document, please visit https://www.apogeesemi.com.

### 7 Legal

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### References

- [1] TSI 180nm CMOS Process (1.8V & 5V)-http://www.tsisemi.com/process/
- [2] Exposure Report, VPTrad, February 6, 2020 (available upon request and appended here)
- [3] Bruker BioSpin e-scan https://www.bruker.com/products/mr/epr/e-scan.html
- [4] Instruction Manual, Gammacell 220 Cobalt 60 Irradiation Unit https://www.nrc.gov/docs/ML0216/ML021630449.pdf
- [5] Department of Defense, Test Method Standard, Environmental Test Methods for Microcircuits, MIL-STD-883-1, Part 1: Test Methods 1000-1999 https://quicksearch.dla.mil/Transient/57DC2ED445914404AE4805799B6BD99A.pdf
- [6] Agilent 4156B Precision Semiconductor Parameter Analyzer, User's Guide Volume 2, Measurement and Analysis https://mntl.illinois.edu/facilities/device-characterization/ equipment/documents/Agilent4155Buserguide.pdf



# A Calibration Certificates

simco	-•		Certificate No. 8788	829				
electroni 783 N. GROVE ROAD, STE. 106 RICHARDSON, TX 75081		SITTE						
RICHARDSON, TX 75081 ON SITE CERTIFICATE OF CALIBRATION FOR								
APOGEE SEMICONDUCTOR 538 HAGGARD ST. PLANO, TX 75074								
Description: KEITHLEY, 2400, Sou	irce Meter							
Serial No: 1192264	Asset No:	SMU1	SIMCO ID: 57647-325					
Dept: NONE	PO No: 200	2						
Calibration Date: 12/04/2019	Calibration Inter	val: 12 Months	Next Calibration Date: 12/04/20	20				
Arrival Condition: MEETS MANUFACTURER'S SPE	EC'S.	Service: CALIBRATED T	O MFR SPEC, & CLEAN					
Procedure: 2400-902-01 REV D Temperature: 72°F		Re	lative Humidity: <b>29.2</b> %					
Standards Used: <u>Manufacturer, Model</u> FLUKE, 5450A AGILENT, 34410A OMEGA ENGINE ERING, RH82	<u>Description</u> Resistance Calibra Digital Multimeter Thermo Hygromet	ator 1	IMCO ID Due Date Certifica 5940-812 11/16/2020 8664094 5940-748 09/10/2020 8694770 5940-421 10/24/2020 8734655	4 0				
There are 2 Supplementary Data She	eet(s) attached.							
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Work performed by: Gregory Bender SIMCO Electronics' quality management system are performed using internationally recognized s calibrations by the National Institute of Standard constants, intrinsic standards or ratio calibration measurement uncertainty analysis and/or guard to the instrument identified above and may not b warranty that the instrument will maintain its spe beyond our control.	n conforms to ISO 9001.201 tandards traceable to the Int Is and Technology (NIST), of techniques. Instruments are bands are applied during the reproduced, except in full.	Daniel Beights 5, ISO/IEC 17025:2017, ; emational System of Unit ther National Measureme calibrated with a test uno measurement process. Ti without prior written con	s (SI Units). Traceability is achieved through nt Institutes (NMIs'), or by using natural phys ertainty ratio of 4:1 or greater, otherwise information shown on this certificate applie sent from SIMCO Electronics. There is no in	sical es only				
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Description: KEITHLEY, 2400, Sou	rce Meter							
Serial No: 4076934	Asset No: SM	U0	SIMCO ID: 57	647-324				
Dept: NONE	PO No: 2002		1					
Calibration Date: 12/04/2019	Calibration Interva	l: 12 Months	Next Calibration Da	ite: 12/04/2020				
Arrival Condition: MEETS MANUFACTURER'S SPE		Service: CALIBRATED T	O MFR SPEC, & CLE	AN				
Procedure: 2400-902-01 REV D Temperature: 72°F Standards Used: <u>Manufacturer, Model</u> FLUKE, 5450A AGILENT, 34410A OMEGA ENGINEERING, RH82	<u>Description</u> Resistance Calibrato Digital Multimeter Thermo Hygrometer	or 1 1	Elative Humidity: 29.2 SIMCO ID Due Date 15940-812 11/16/20 15940-748 09/10/20 15940-421 10/24/20	e <u>Certificate</u> 20 8664094 20 8694770				
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SIMCO Electronics' quality management system are performed using internationally recognized s calibrations by the National Institute of Standard constants, intrinsic standards or ratio calibration measurement uncertainty analysis and/or guard b to the instrument identified above and may not b warranty that the instrument will maintain its spe beyond our control. Dated: 12/04/2019	tandards traceable to the Intern is and Technology (NIST), other techniques. Instruments are ca bands are applied during the me is reproduced, except in full, with	ational System of Unit er National Measureme librated with a test und asurement process. T ithout prior written cor	ts (SI Units). Traceability is ent Institutes (NMIs'), or by u certainty ratio of 4:1 or greate he information shown on this nsent from SIMCO Electronic	achie ved through ising natural physical er, otherwise certificate applies only is. There is no implied				



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Description: KEITHLEY, 2400, Sou	rce Meter							
Serial No: 4300766	Asset No: SMU4	SIMCO ID: 57647-323						
Dept: NONE	PO No: 2002							
Calibration Date: 12/04/2019	Calibration Interval: 12 Months	Next Calibration Date: 12/04/2020						
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Procedure: 2400-902-01 REV D Temperature: 72°F Standards Used: <u>Manufacturer, Model</u> FLUKE, 5450A AGILENT, 34410A OMEGA ENGINEERING, RH82	Description 5 Resistance Calibrator 1	Elative Humidity: <b>29.2</b> % <u>SIMCO ID</u> <u>Due Date</u> <u>Certificate</u> 15940-812 11/16/2020 8664094 15940-748 09/10/2020 8694770 15940-421 10/24/2020 8734655						
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Work performed by: Gregory Bender SIMCO Electronics' quality management system are performed using internationally recognized st calibrations by the National Institute of Standard: constants, intrinsic standards or ratio calibration ti measurement uncertainty analysis and/or guard b to the instrument identified above and may not be	Reviewed by: Daniel Beights a conforms to ISO 9001:2015, ISO/IEC 17025:2017, tandards traceable to the International System of Uni s and Technology (NIST), other National Measurems techniques. Instruments are calibrated with a test un	ts (SI Units). Traceability is achieved through ent Institutes (NMIs'), or by using natural physical certainty ratio of 4:1 or greater, otherwise he information shown on this certificate applies only nsent from SIMCO Electronics. There is no implied						



Procedure: 2400-902-01 REV D Temperature: 72°F R Standards Used: <u>Manufacturer, Model Description</u> FLUKE, 5450A Resistance Calibrator OMEGA ENGINEERING, RH82 Thermo Hygrometer W/Dew Point	Certificate No. 8788826 electronics 783 N. GROVE ROAD, STE. 106 RICHARDSON, TX 75081 ON SITE CERTIFICATE OF CALIBRATION FOR APOGEE SEMICONDUCTOR 538 HAGGARD ST. PLANO, TX 75074								
Dept: NONE PO No: 2002   Calibration Date: 12/04/2019 Calibration Interval: 12 Months   Arrival Condition: Service: CALIBRATED   MEETS MANUFACTURER'S SPEC'S. CALIBRATED   Procedure: 2400-902-01 REV D   Temperature: 72°F R   Standards Used: Manufacturer, Model Description   FLUKE, 5450A Resistance Calibrator   OMEGA ENGINEERING, RH82 Thermo Hygrometer W/Dew Point   AgiLENT, 34410A Digital Multimeter									
Calibration Date: 12/04/2019 Calibration Interval: 12 Months   Arrival Condition: MEETS MANUFACTURER'S SPEC'S. Service: CALIBRATED   Procedure: 2400-902-01 REV D Temperature: 72°F R   Standards Used: Manufacturer, Model Description Resistance Calibrator   OMEGA ENGINE ERING, RH82 Thermo Hygrometer W/Dew Point AGILENT, 34410A Digital Multimeter   There are 2 Supplementary Data Sheet(s) attached. Work performed by: Reviewed by: Daniel Beights   SIMCO Electronics' quality management system conforms to ISO 9001 2015, ISO/IEC 17025/2017 are performed using internationally recognized standards traceable to the International System of Uz calibrations by the National Institute of Standards and Technology (NIST), other National Measurem constants, intrinsic standards or ratio calibration techniques. Instruments are calibratement process. Simultanet identified above and may not be reproduced, except in full, without prior writter or the network are applied during the measurement process.	SIMCO ID: 57647-322								
Arrival Condition: Service:   MEETS MANUFAC TURER'S SPEC'S. CALIBRATED   Procedure: 2400-902-01 REV D   Temperature: 72°F   R Standards Used:   Manufacturer, Model Description   FLUKE, 5450A Resistance Calibrator   OMEGA ENGINE ERING, RH82 Thermo Hygrometer W/Dew Point   AGILENT, 34410A Digital Multimeter									
MEETS MANUFACTURER'S SPEC'S.   CALIBRATED     Procedure: 2400-902-01 REV D Temperature: 72°F   R     Standards Used: Manufacturer, Model   Description Resistance Calibrator OMEGA ENGINEERING, RH82 AGILENT, 34410A   Resistance Calibrator Thermo Hygrometer W/Dew Point Digital Multimeter     There are 2 Supplementary Data Sheet(s) attached.   Work performed by: Gregory Bender   Reviewed by: Daniel Beights     SIMCO Electronics' quality management system conforms to ISO 9001-2015, ISO/IEC 17025-2017 are performed using internationally recognized standards traceable to the International System of Ur calibrations by the National Institute of Standards and Technology (NIST), other National Measurem constants, intrinsic standards or ratio calibration techniques. Instruments are calibrated with a test u measurement uncertainty analysis and/or guard bands are applied during the measurement process.	Next Calibration Date: 12/04/2020								
Temperature: 72°F R   Standards Used: Manufacturer, Model Description   FLUKE, 5450A Resistance Calibrator   OMEGA ENGINEERING, RH82 Thermo Hygrometer W/Dew Point   AGILENT, 34410A Digital Multimeter	TO MFR SPEC, & CLEAN								
Manufacturer, Model Description   FLUKE, 5450A Resistance Calibrator   OMEGA ENGINE ERING, RH82 Thermo Hygrometer W/Dew Point   AGILENT, 34410A Digital Multimeter	Relative Humidity: 29.2%								
Work performed by: Gregory Bender Reviewed by: Daniel Beights   SIMCO Electronics' quality management system conforms to ISO 9001 2015, ISO/IEC 17025 2017 are performed using internationally recognized standards traceable to the International System of Ur calibrations by the National Institute of Standards and Technology (NIST), other National Measurem constants, intrinsic standards or ratio calibration techniques. Instruments are calibrated with a test us measurement uncertainty analysis and/or guard bands are applied during the measurement process. to the instrument identified above and may not be reproduced, except in full, without prior written cor	SIMCO ID   Due Date   Certificate     15940-812   11/16/2020   8664094     15940-421   10/24/2020   8734655     15940-748   09/10/2020   8694770								
Gregory Bender Daniel Beights SIMCO Electronics' quality management system conforms to ISO 9001:2015, ISO/IEC 17025:2017 are performed using internationally recognized standards traceable to the International System of Un calibrations by the National Institute of Standards and Technology (NIST), other National Measurem constants, intrinsic standards or ratio calibration techniques. Instruments are calibrated with a test un measurement uncertainty analysis and/or guard bands are applied during the measurement process. to the instrument identified above and may not be reproduced, except in full, without prior written co									
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beyond our control. Dated: 12/04/2019	Inits (SI Units). Traceability is achieved through ment Institutes (NMIs <sup>2</sup> ), or by using natural physical uncertainty ratio of 4:1 or greater, otherwise The information shown on this certificate applies only consent from SIMCO Electronics. There is no implied								
Page 1 of 1									

Certificate No. 8935524



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		elec	tronics

783 N. GROVE ROAD, STE. 106 RICHARDSON, TX 75081

#### ON SITE STATEMENT OF WORK FOR APOGEE SEMICONDUCTOR 538 HAGGARD ST. PLANO, TX 75074

Description: TEST EQUITY, FS2-1, Oven

Serial No: 12140106

Asset No:

SIMCO ID: 57647-9

Dept: NONE

PO No: 2002

Service Date: 04/24/2020	Calibration Interval:	Next Calibration Date:
Arrival Condition: OUT OF SPECIFICATION	Service	e: RN "AS-IS"(RAI)-FAILED CAL

Procedure: 010-0090 REV 5 Temperature: 68°F

Relative Humidity: 36%

Standards Used:

Certificate Manufacturer, Model SIMCO ID Due Date Description ONSET COMPUTER CORP, ZW-003 Temperature/Humidity Logger 15940-1023 09/30/2020 8646941 OMEGA ENGINEERING, CL23A THERMOMETER CALIBRATOR 15940-680 08/21/2020 8661776

Detail Of Work Performed:

UNIT IS OOT AND NOT LINEAR. RAI AT OWNER REQUEST

Calibration Data:	* denotes an out of tolerance data point			
Parameter	Nominal	Measured Before	Measured After	Tolerance
TEMP	100.0 C	80.8	80.8	+/-5 C
TEMP	*125.0 C	103.8	103.8	+/-5 C
RISE TIME	•			
<15MIN	*PASS	0	0	1=PASS0=FAIL

There are 1 Supplementary Data Sheet(s) attached.

Work performed by:	Reviewed by:	
Peter Alexeichik	David Whitley	

SIMCO Electronics' quality management system conforms to ISO 9001 2015, ISO/IEC 17025 2017, and ANSI/NCSL Z540-1-1994. All calibrations are performed using internationally recognized standards traceable to the International System of Units (SI Units). Traceability is achieved through calibrations by the National Institute of Standards and Technology (NIST), other National Measurement Institutes (NMIs'), or by using natural physical constants, intrinsic standards or ratio calibration techniques. Instruments are calibrated with a test uncertainty ratio of 4:1 or greater, otherwise measurement uncertainty analysis and/or guard bands are applied during the measurement process. The information shown on this certificate applies only to the instrument identified above and may not be reproduced, except in full, without prior written consent from SIMCO Electronics. There is no implied warranty that the instrument will maintain its specified tolerances during the calibration interval due to possible drift, environment, or other factors be yond our control.

Dated: 04/24/2020

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